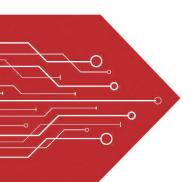
MSKSEMI















ESD

TVS

TSS

MOV

GDT

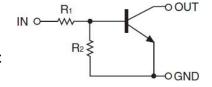
PLED

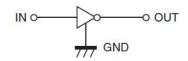
Broduct data sheet

FEATURES

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors(see equivalent circuit)
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation, making device design easy

Equivalent Circuit

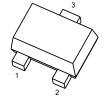




● P/N	MARK
DTC114EM	24
DTC114EE	24
DTC114EUA	24
DTC114EKA	24
DTC114ECA	24

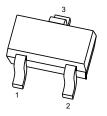
PIN CONNENCTIONS

DTC114EM SOT-723



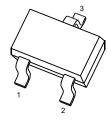
1. IN 2. GND 3. OUT

DTC114EE SOT-523



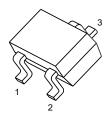
1. IN
 2. GND
 3. OUT

DTC114EUA SOT-323



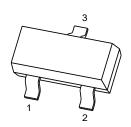
1. IN 2. GND 3. OUT

DTC114EKA SOT-23-3L



1. IN 2. GND 3. OUT

DTC114ECA SOT-23



1. IN 2. GND 3. OUT

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	DTC114EXX			Unit		
- Cyllibol	raidilleter	EM	EE	EUA	EKA	ECA	Onit
Vcc	Supply Voltage		50				V
V _{IN}	Input Voltage		-10∼+40			V	
lo	Output Current	50			mA		
I _{CM}	Peak Collector Current	100				mA	
P _D	Power Dissipation	100 150 200			mW		
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55∼+150			℃		

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

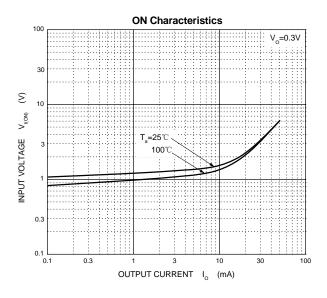
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input voltage	V _{I(off)}	V _{CC} =5V,I _O =100μA	0.5			V
Input voltage	V _{I(on)}	V _O =0.3V,I _O =10mA			3	V
Output voltage	$V_{O(on)}$	I _O /I _I =10mA/0.5mA			0.3	V
Input current	lı	V _I =5V			0.88	mA
Output current	I _{O(off)}	V _{CC} =50V,V _I =0			0.5	μA
DC current gain	Gı	Vo=5V,lo=5mA	30			
Input resistance	R ₁		7	10	13	kΩ
Resistance ratio	R ₂ /R ₁		0.8	1	1.2	
Transition frequency	f⊤	V ₀ =10V,I ₀ =5mA,f=100MHz		250		MHz

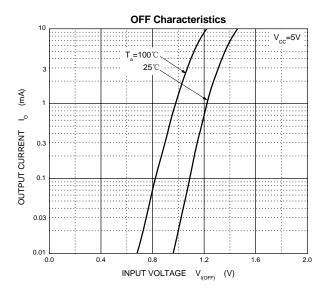


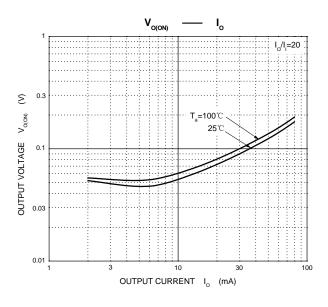


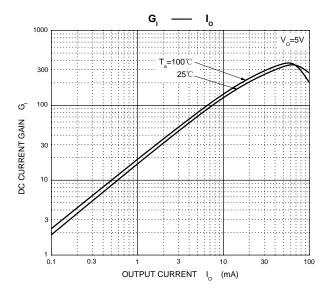


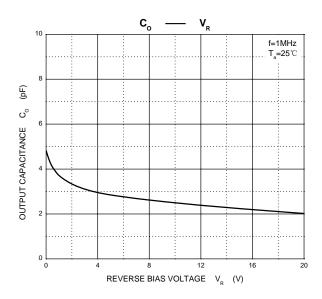
Typical Characteristics

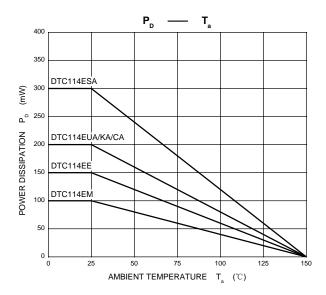




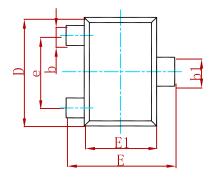


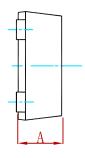


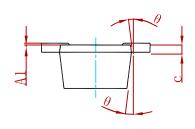






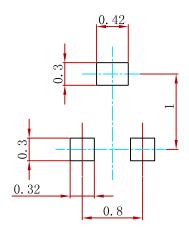






Cumbal	Dimensions In Millimeters		Dimension	ns In Inches
Symbol	Min.	Max.	Min.	Max.
Α	0.430	0.500	0.017	0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
С	0.080	0.150	0.003	0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
е	0.800TYP.		0.03	1TYP.
A	7° RFF		7°	RFF

Suggested Pad Layout



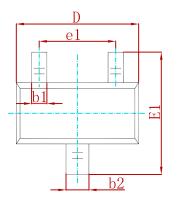
Note:

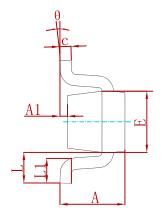
- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

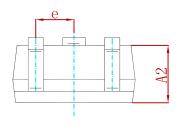
P/N	PKG	QTY
DTC114EM	SOT-723	8000





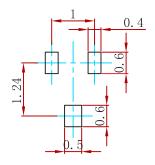






Cumbal	Dimensions	In Millimeters	Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
Α	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
С	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
е	0.500	TYP.	0.020	TYP.
e1	0.900	1.100	0.035	0.043
L	0.400	REF. 0.016 REF.		REF.
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

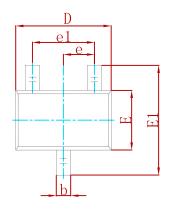
Suggested Pad Layout

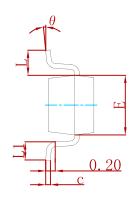


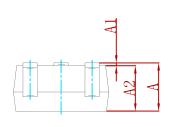
- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

1			
	P/N	PKG	QTY
	DTC114EE	SOT-523	3000



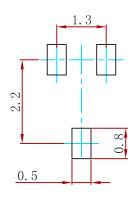






Symbol	Dimensions	Dimensions In Millimeters		s In Inches
Symbol	Min	Max	Min	Max
Α	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
С	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
е	0.650 TYP		0.026	S TYP
e1	1.200	1.400	0.047	0.055
L	0.525	REF	0.021	REF
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout

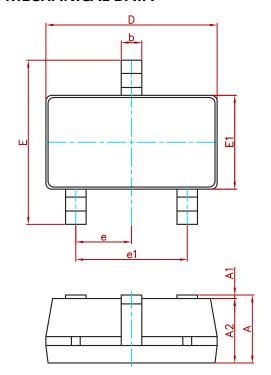


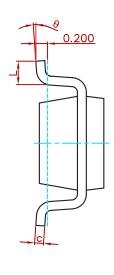
- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

P/N	PKG	QTY
DTC114EUA	SOT-323	3000



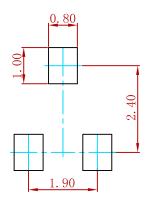






Symbol	Dimensions In	n Millimeters	Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
е	0.950(BSC)	0.037((BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Pad Layout

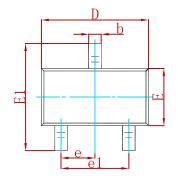


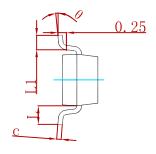
- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

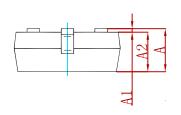
P/N	PKG	QTY
DTC114EKA	SOT-23-3L	3000





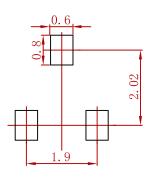






Symbol	Dimensions	In Millimeters	Dimension	s In Inches
Symbol	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.95	0 TYP	0.037	7 TYP
e1	1.800	2.000	0.071	0.079
L	0.55	0.550 REF		2 REF
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



- 1.Controlling dimension:in millimeters. 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

P/N	PKG	QTY
DTC114ECA	SOT-23	3000



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